REMARKS

Present Status of the Application

The Advisory Office Action indicates a new matter "the mechanical support structure 112 is disposed over a non-device section 120". Applicant has removed the new matter. After entry of the foregoing amendments, claims 1-15 remain pending in the present application, and reconsideration of those claims is respectfully requested.

Discussion of Office Action Rejections

The Office Action indicates a new matter "the mechanical support structure 112 is disposed over a non-device section 120". Applicant has removed the new matter, which is indicated by the Office Action.

In the previous response to the Final Action, Applicant has provided the reason to respectfully traverse the new matter. It is believed that the above "new matter" indicated by the Office Action is actually not the new matter.

However, Applicant has amended claims 1 and 8 based on [0009] lines 23. It is believed that the issue of new matter has been overcome by the newly amendments.

CONCLUSION

For at least the foregoing reasons, it is believed that all pending claims 1-15 are in proper condition for allowance. If the Examiner believes that a telephone conference would expedite

the examination of the above-identified patent application, the Examiner is invited to call the undersigned.

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Dated: Dec. 18, 2002

By: _____

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VERSION WITH MARKINGS TO SHOW WHERE CHANGES MADE

In The Specification

Please cancel the previous amendment on [0021] in the previous response filed Oct. 18, 2002, and therefore [0021] remain the same as the original specification.

In The claims

Please amend claims 1 and 8 as follows:

1. (Thrice Amended) A bonding pad structure, comprising:

a substrate having at least a device section and a non-device section;

a bonding pad layer above the substrate;

a current conduction structure over the device section, between the bonding pad layer and the substrate for connecting the bonding pad layer and the substrate electrically, wherein the current conduction structure includes:

a plurality of conductive metallic layers, wherein each conductive metallic layer is at a different height level from the substrate; and

a plurality of conductive plugs for linking neighboring conductive metallic layers and the conductive metallic layers with the bonding pad layer and the substrate;

a mechanical support structure [over the non-device section]connecting with the non-device section of the substrate, between the bonding pad layer and the substrate, wherein the mechanical support structure includes:

a plurality of support metallic layers, wherein each support metallic layer is at a different height level from the substrate; and

a plurality of support plugs for linking up neighboring support metallic layers and the support metallic layers with the bonding pad layer and the substrate; and

an insulation layer between the bonding pad layer, the current conduction structure, the mechanical support structure and the substrate for isolating the current conduction structure from the mechanical support structure.

8. (Thrice amended) A bonding pad structure, comprising:

a substrate having at least a device section and a non-device section;

a bonding pad layer above the substrate;

a current conduction structure over the device section, between the bonding pad layer and the substrate for connecting the bonding pad layer and the substrate electrically, wherein the current conduction structure includes:

a plurality of conductive metallic layer, wherein each conductive metallic layer is at a different height level from the substrate and one of the conductive metallic layers is in direct contact with the substrate; and

a plurality of conductive plugs for linking neighboring conductive metallic layers and linking one of the conductive metallic layers with the bonding pad layer;

a mechanical support structure [over the non-device section]connecting with the non-device section of the substrate, between the bonding pad layer and the substrate, wherein the mechanical support structure includes:

a plurality of support metallic layers, wherein each support metallic layer is at a different height level from the substrate and one of the support metallic layers is in direct contact with the substrate; and

a plurality of support plugs for linking neighboring support metallic layers and linking one of the support metallic layers with the bonding pad layer; and

an insulation layer between the bonding pad layer, the current conduction structure, the mechanical support structure and the substrate for isolating the current conduction structure from the mechanical support structure.